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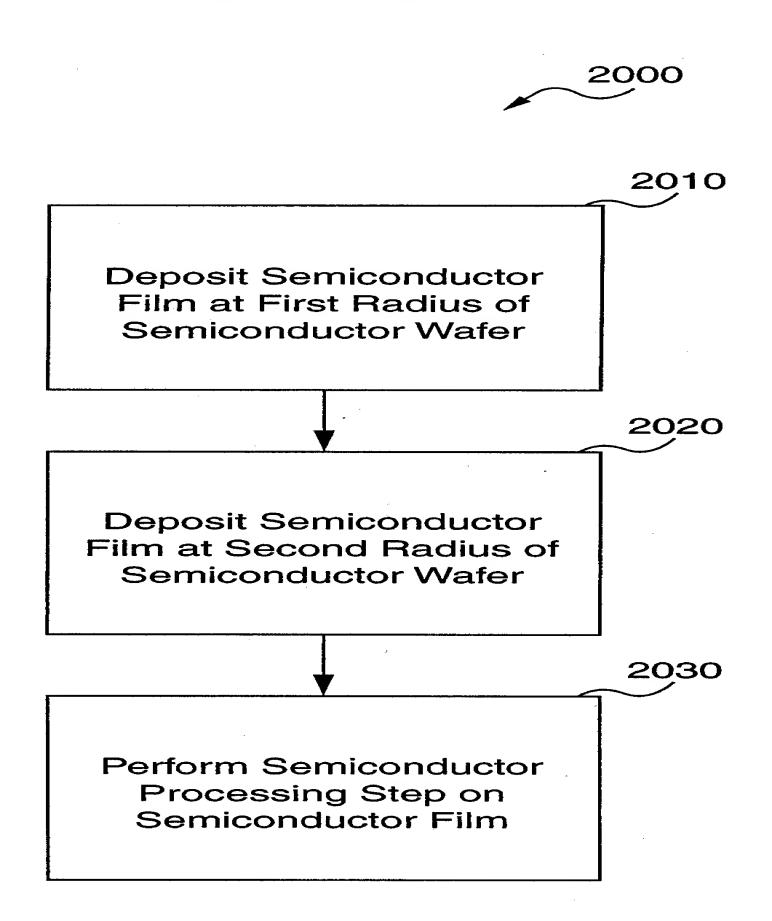
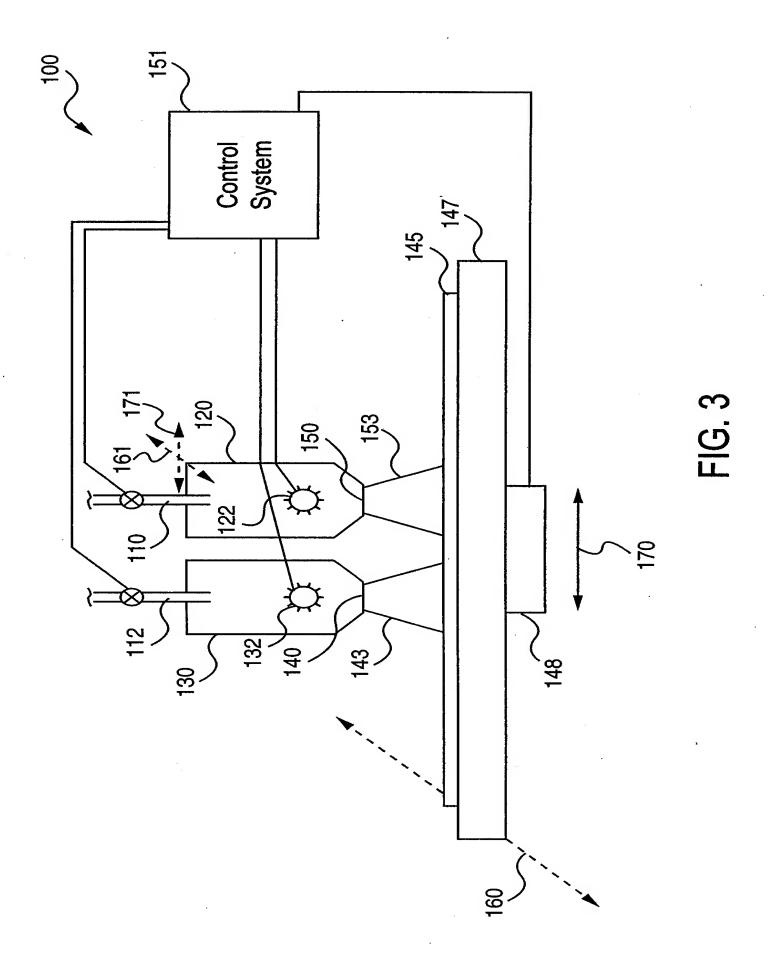


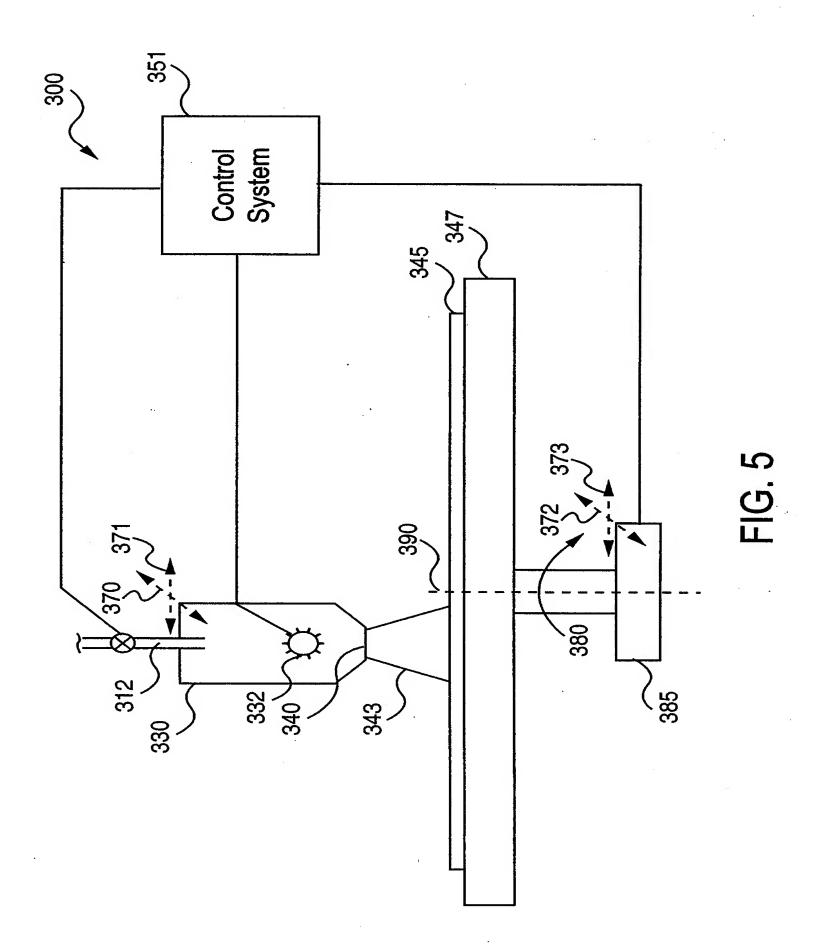
FIG. 1

BU9-99-179 2100 2110 Deposit Semiconductor Film at a First Location on the Semiconductor Wafer, the First Location to Become Part of a First Semiconductor Device 2120 Deposit Semiconductor Film at a Second Location on the Semiconductor Wafer, the Second Location to Become Part of a Second Semiconductor Device 2130 Perform Processing Steps to Create Devices 2140 Measure the two Semiconductor Devices' Device Characteristics 2150 **Determine Optimal Device** Characteristic, Thusly **Determining Best Device** Configuration

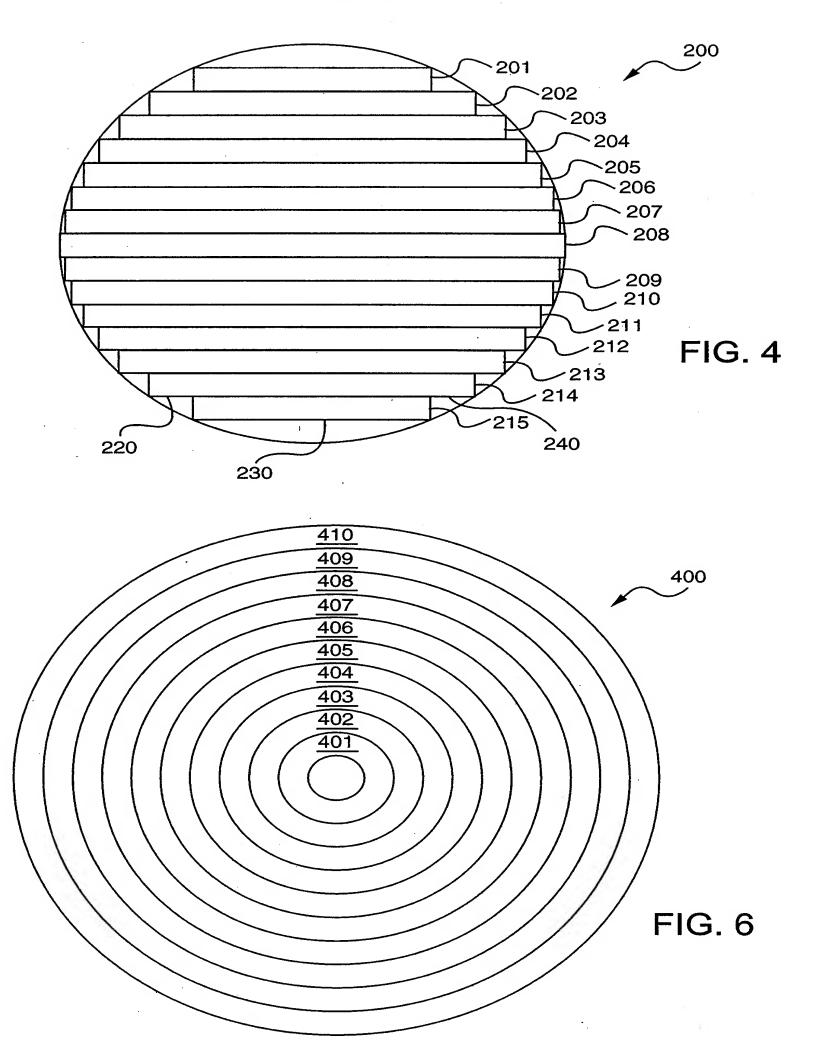
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FIG. 2





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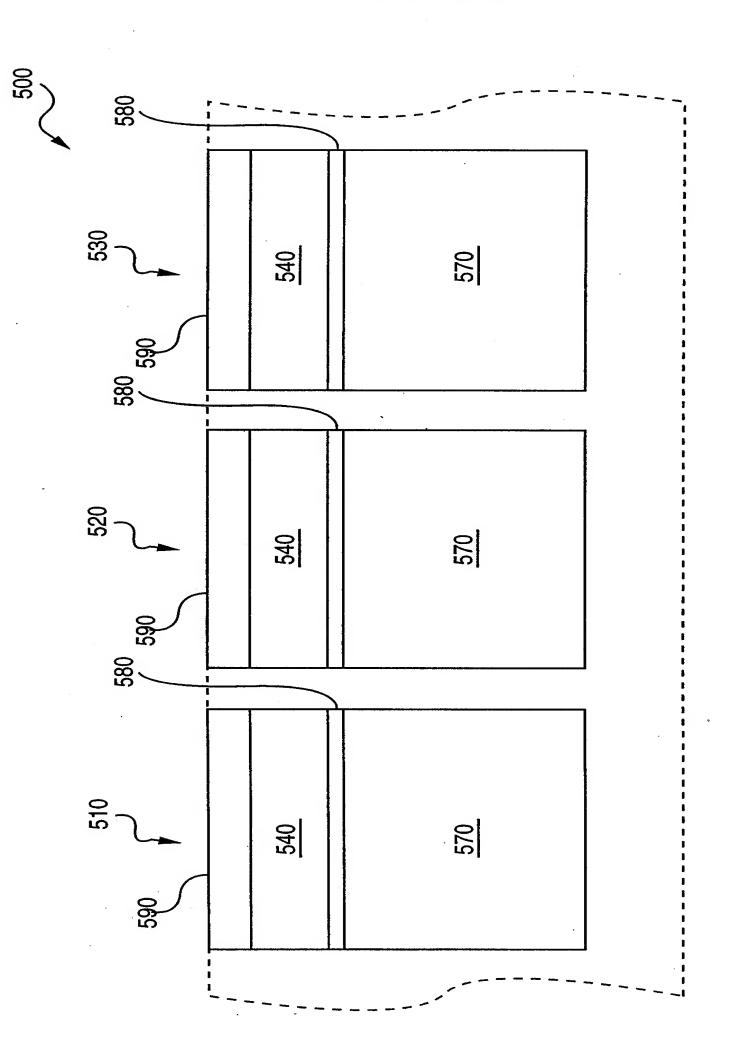


FIG. 7 (PRIOR ART)

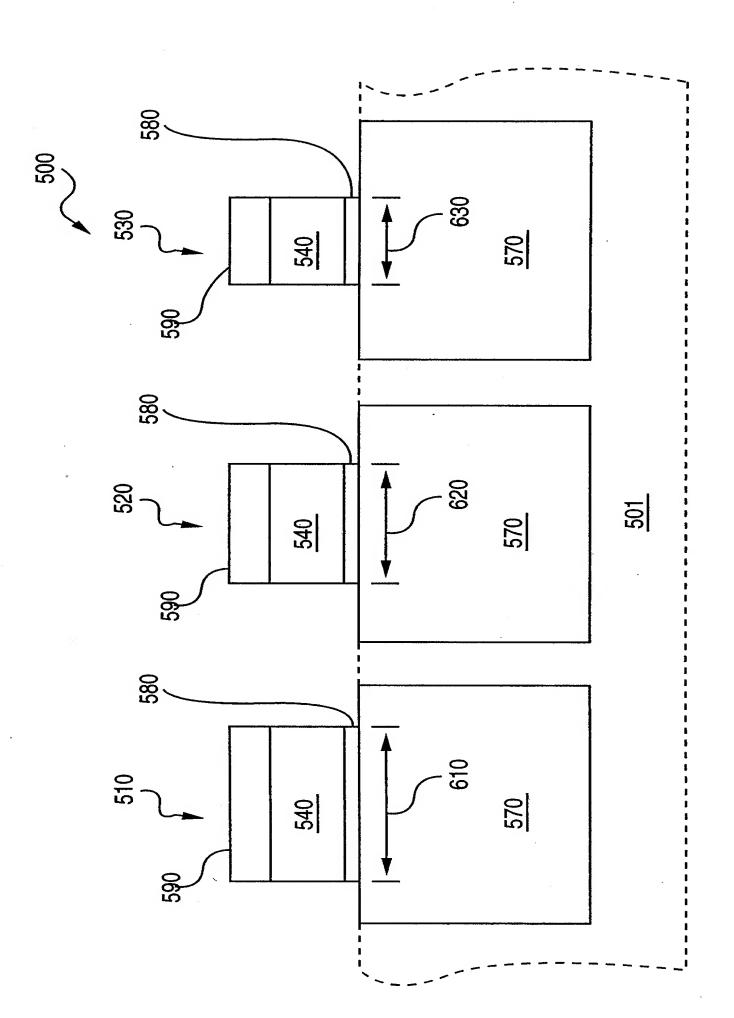


FIG. 8 (PRIOR ART)

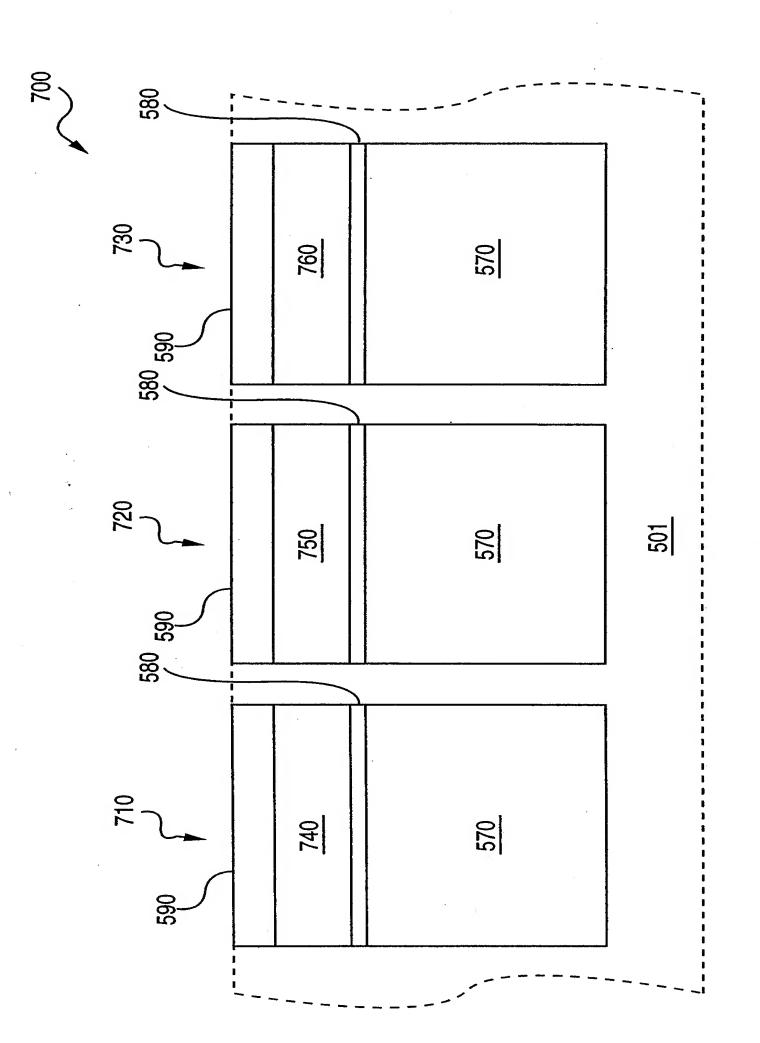
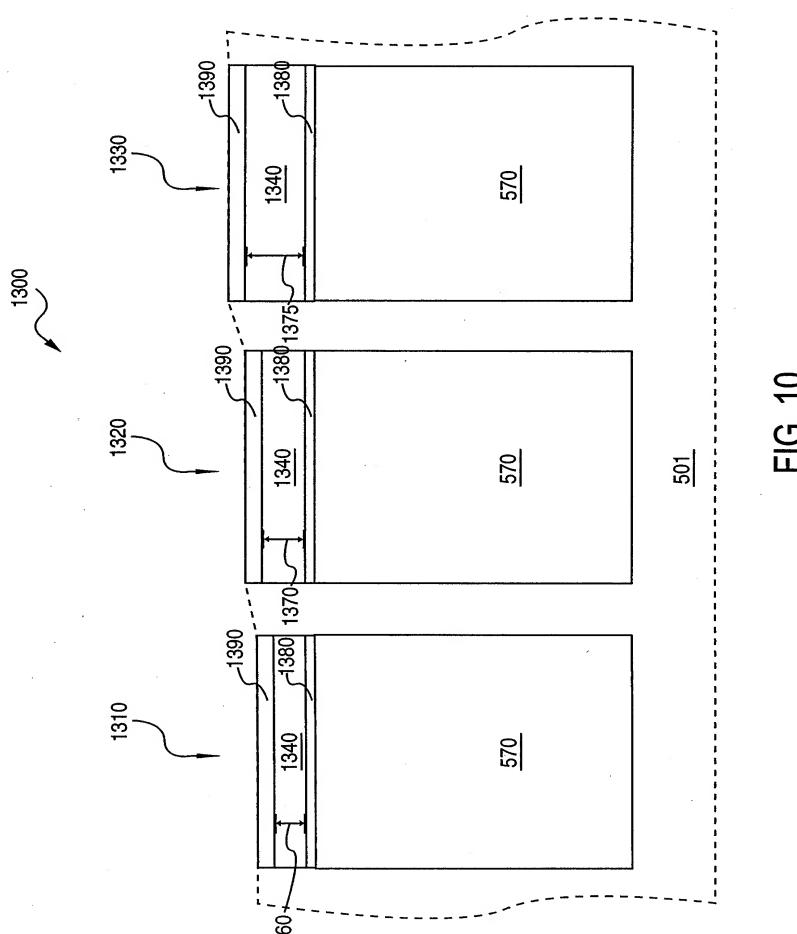
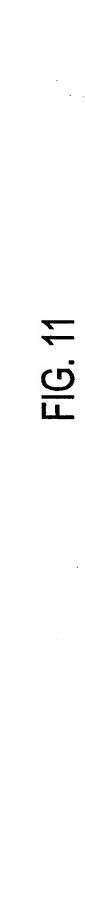
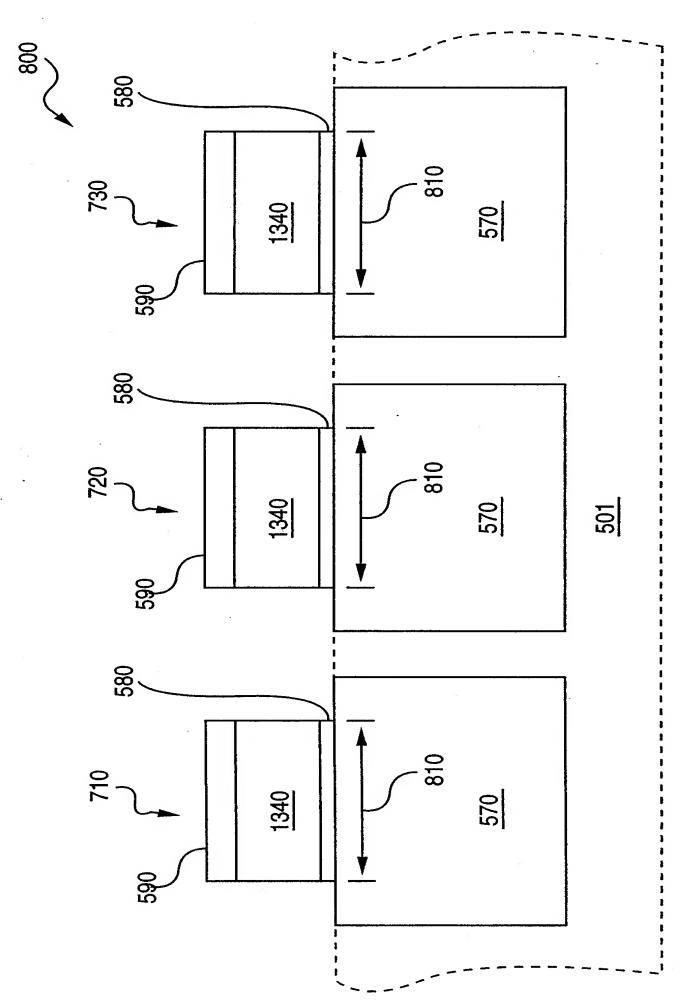


FIG. 9







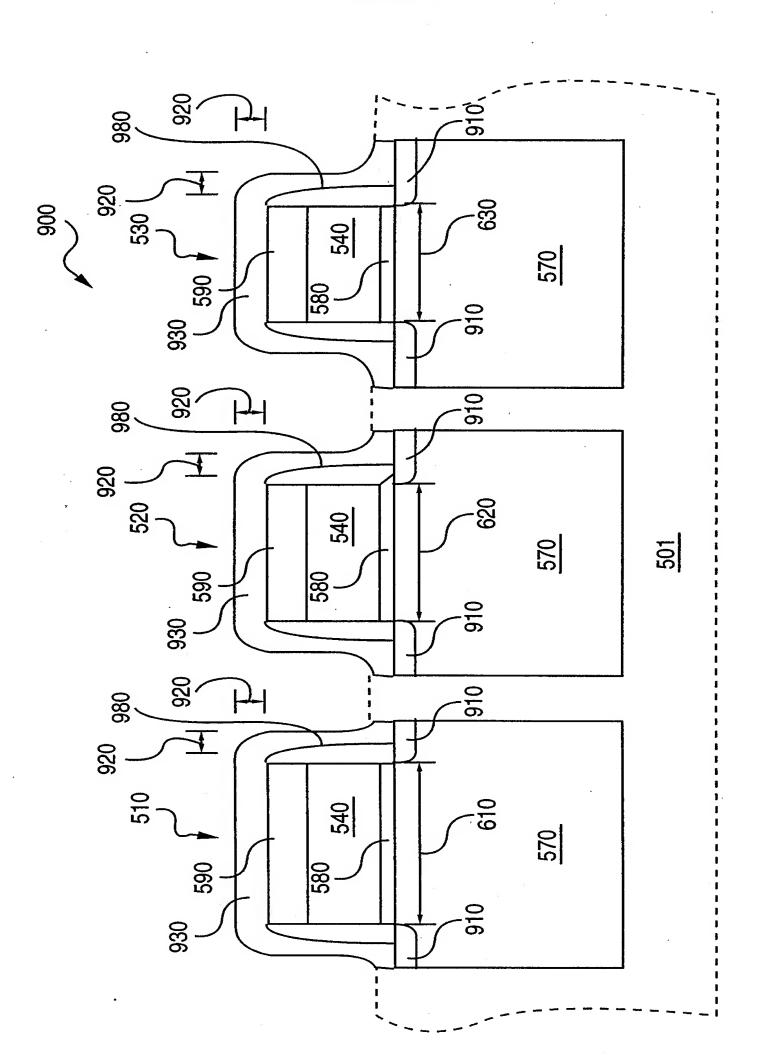


FIG. 12 (PRIOR ART)

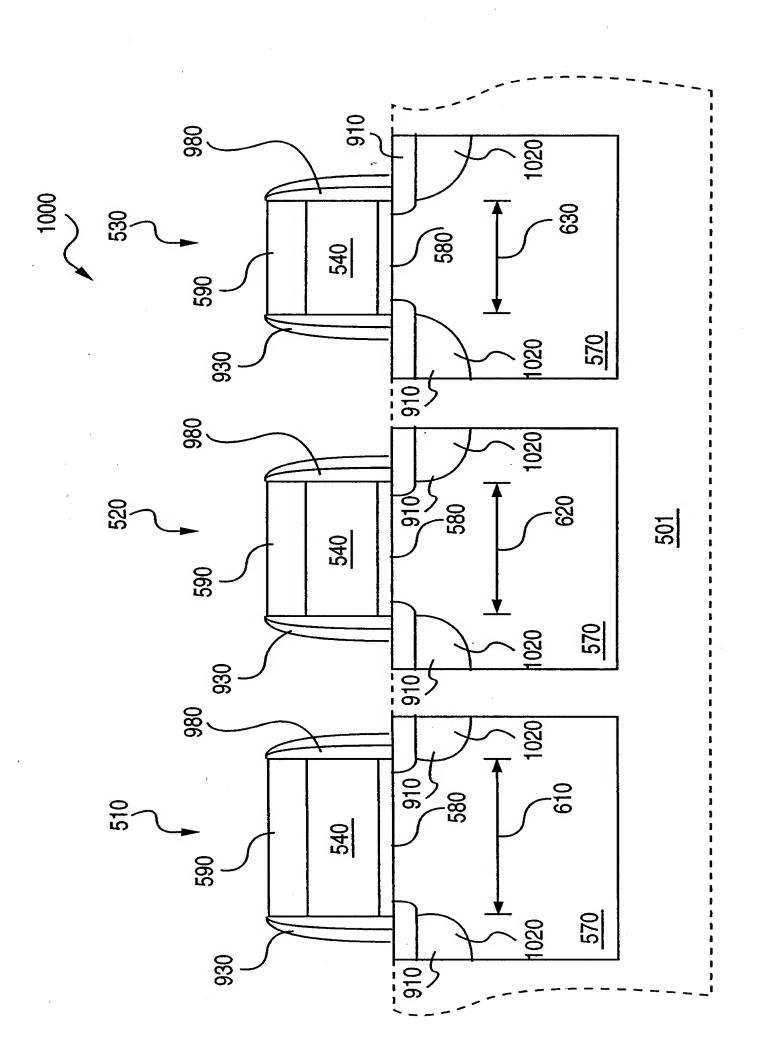


FIG. 13 (PRIOR ART)

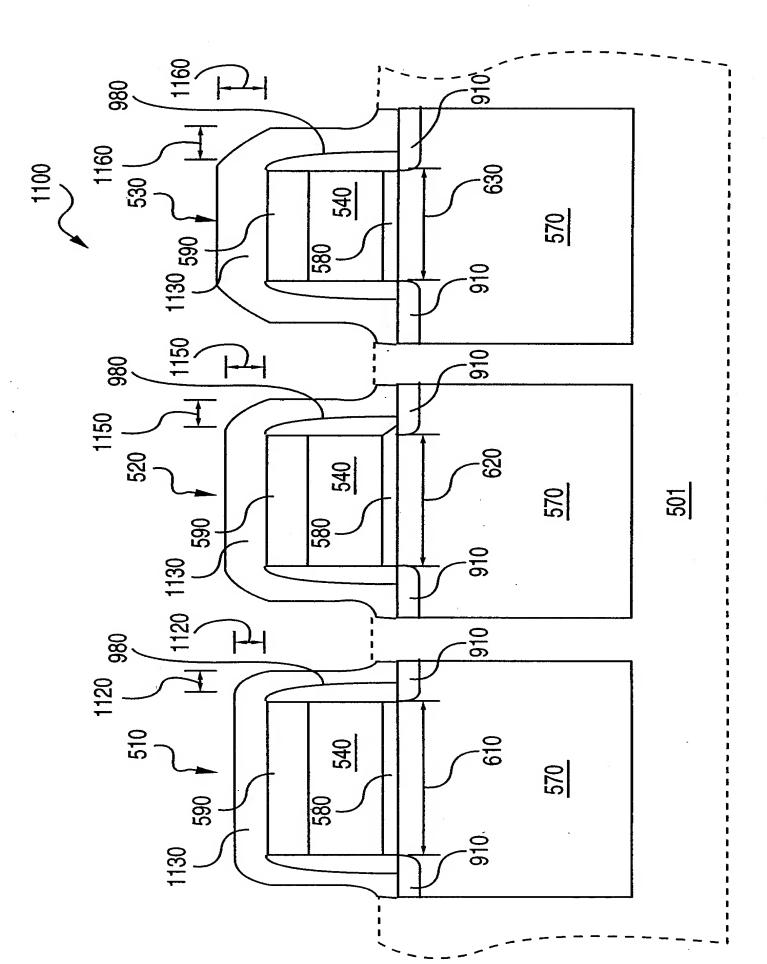


FIG. 14

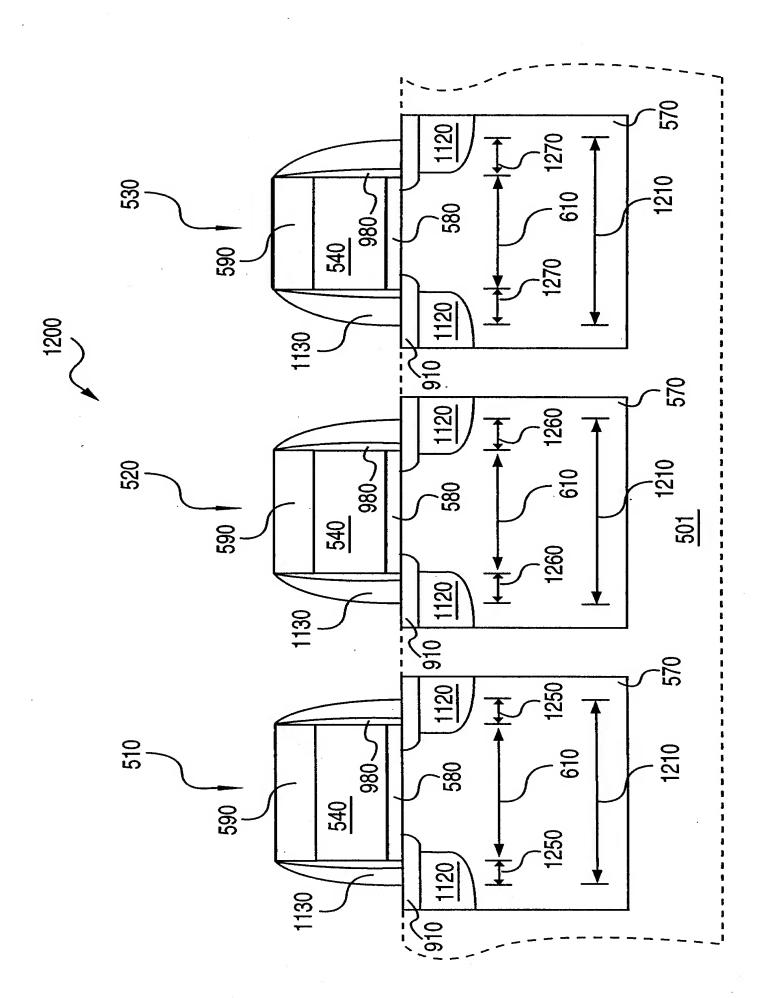


FIG. 15

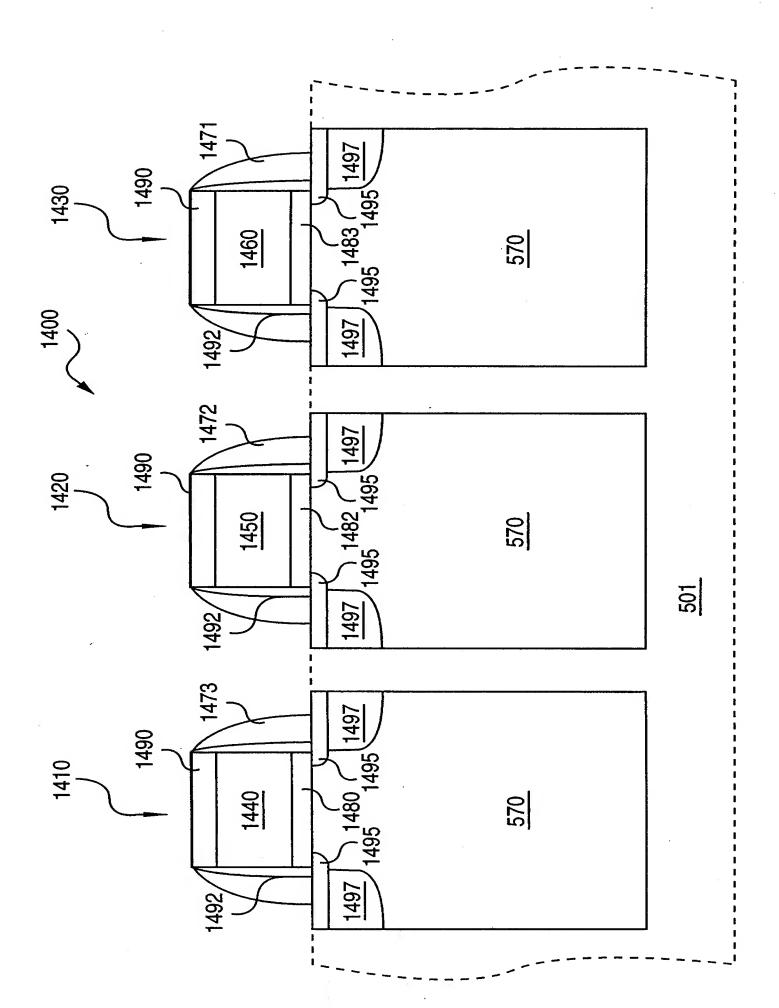


FIG. 16

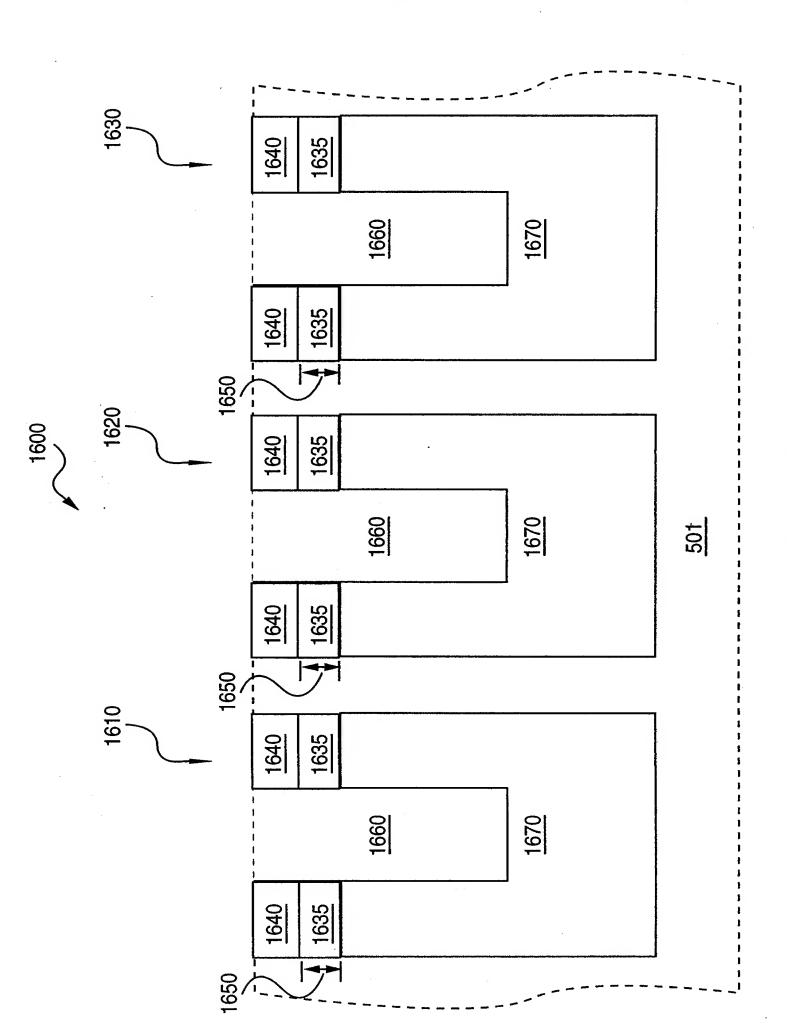


FIG. 17 (PRIOR ART)

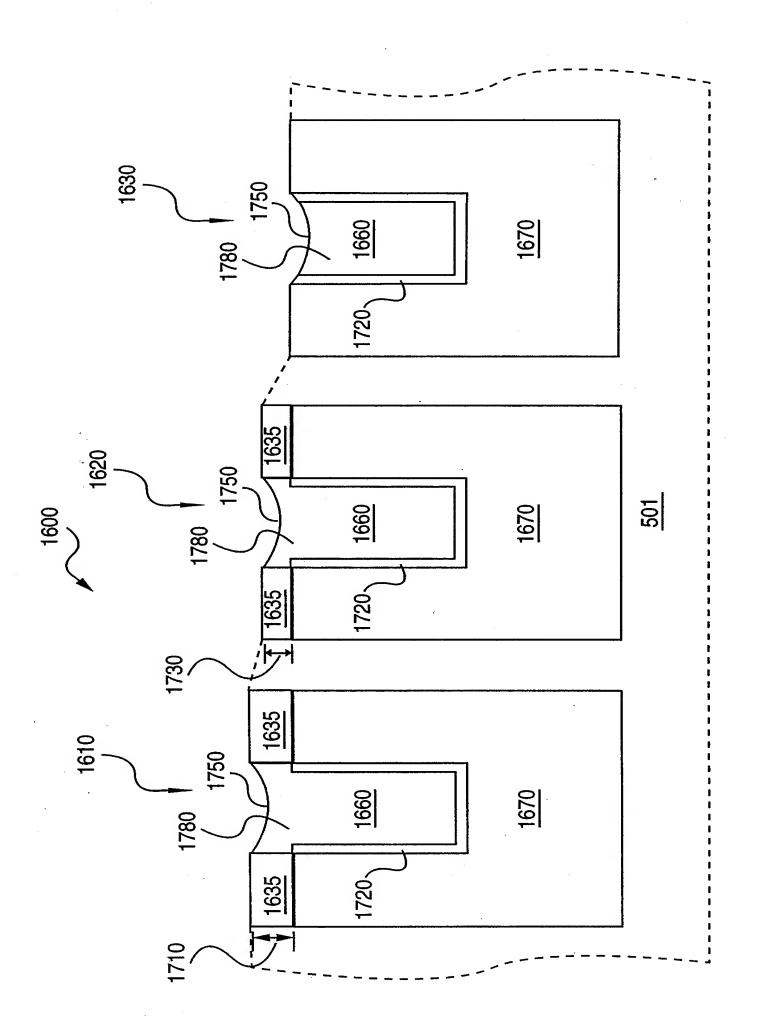
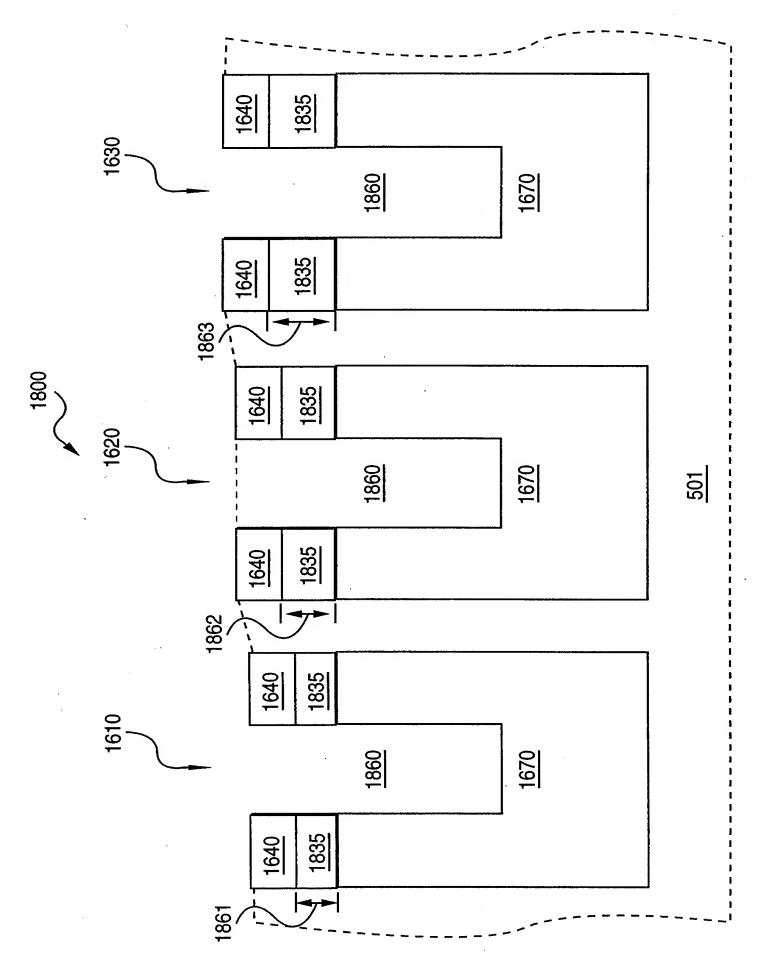


FIG. 18 (PRIOR ART)



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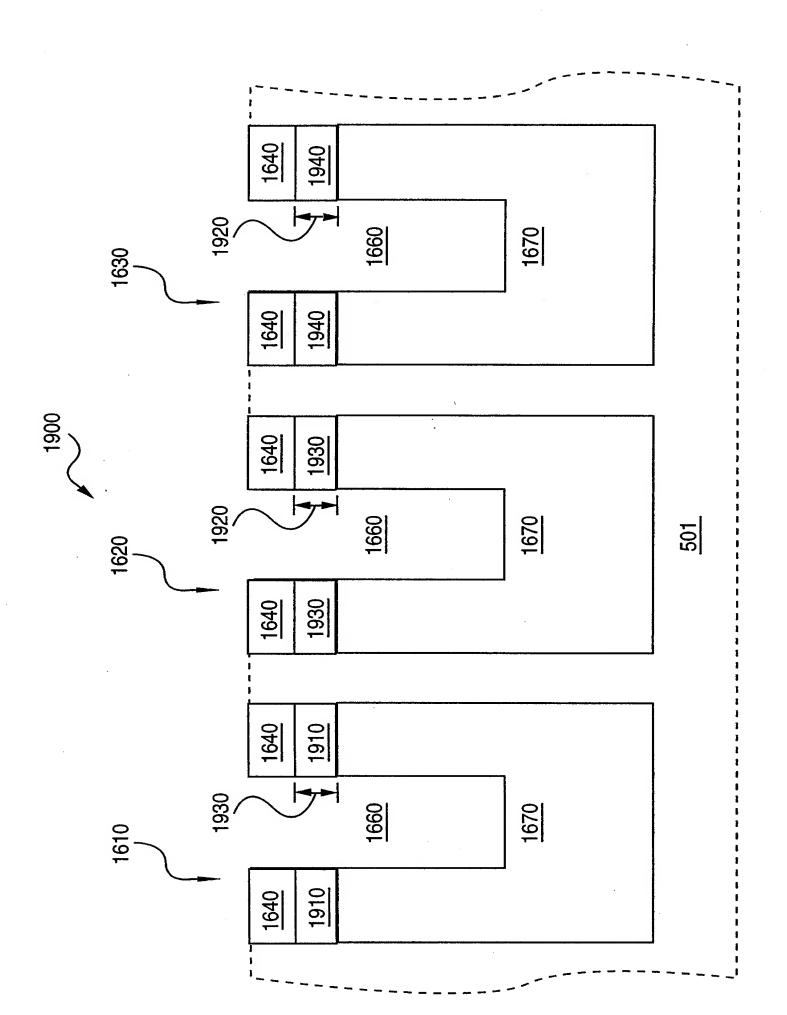


FIG. 20

